2.5 Volt Reference

The CS1009 is a precision trimmed 2.5 V ±5.0 mV shunt regulator diode. The low dynamic impedance and wide operating current range enhances its versatility. The tight reference tolerance is achieved by on-chip trimming which minimizes voltage tolerance and temperature

A third terminal allows the reference voltage to be adjusted $\pm 5.0\%$ to calibrate out system errors. In many applications, the CS1009GZ can be used as a pin-to-pin replacement of the LT1009CZ and the LM136Z-2.5 with the external trim network eliminated.

Features

- 0.2% Initial Tolerance Max.
- Guaranteed Temperature Stability
- Maximum 0.6 Ω Dynamic Impedance
- Wide Operating Current Range
- Directly Interchangeable with LT1009 and LM136 for Improved Performance
- No Adjustments Needed for Minimum Temperature Coefficient
- Meets Mil Std 883C ESD Requirements

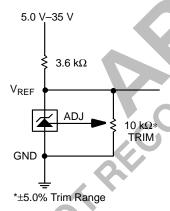


Figure 1. Application Diagram



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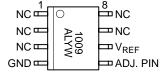
SO-8 **D SUFFIX** CASE 75

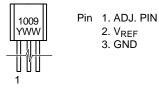


TO-92 Z SUFFIX CASE 29

> 2. V_{RFF} 3. GND

PIN CONNECTIONS AND **MARKING DIAGRAM**





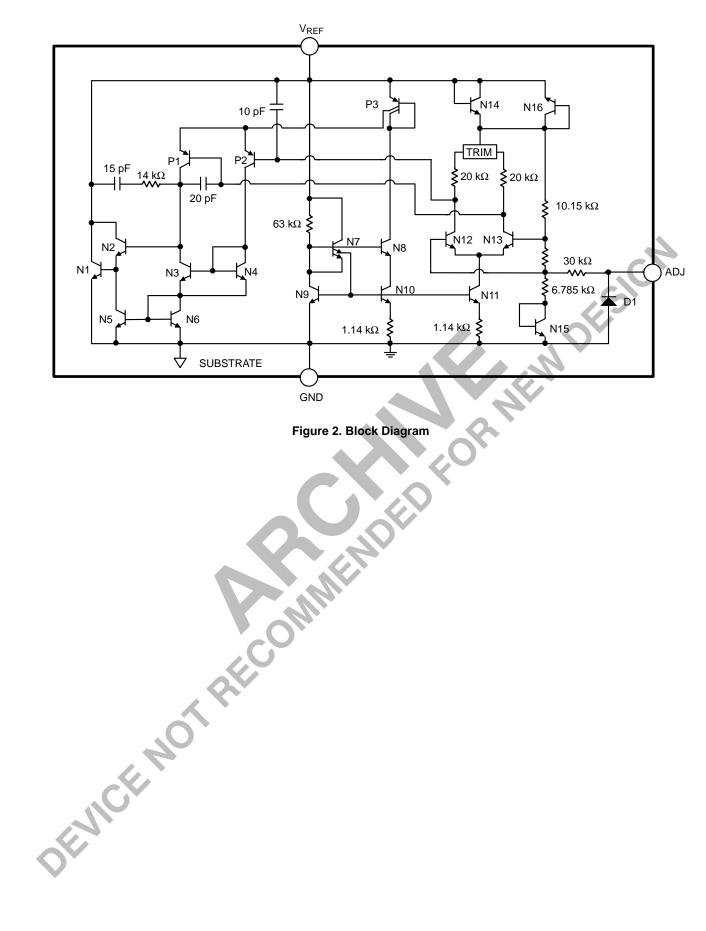
= Assembly Location = Wafer Lot

YY, Y = Year WW. W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
CS1009GD8	SO-8	95 Units/Rail
CS1009GDR8	SO-8	2500 Tape & Reel
CS1009GZ3	TO-92	2000 Units
CS1009GZR3	TO-92	2000 Tape & Reel

SEVICE



MAXIMUM RATINGS*

Rating			Unit
Reverse Current		20	mA
Forward		10	mA
Operating Temperature Range		-40 to 105	°C
Storage Temperature Range		-65 to +150	°C
Lead Temperature Soldering:	Wave Solder (through hole styles only) (Note 1) Reflow: (SMD styles only) (Note 2)	260 peak 230 peak	°C °C

^{1. 10} second maximum

$\textbf{ELECTRICAL CHARACTERISTICS} \quad (T_A = 25^{\circ}\text{C unless otherwise specified.})$

Characteristic	Test Conditions	Min	Тур	Max	Unit
Reverse Breakdown Voltage	I _R = 1.0 mA	2.492	2.500	2.508	V
Reverse Breakdown Voltage	$0^{\circ}\text{C} \le \text{T}_{\text{A}} \le 105^{\circ}\text{C}$	2.492	2.500	2.508	V
Reverse Breakdown Voltage	$-40^{\circ}\text{C} \le \text{T}_{\text{A}} \le ^{\circ}\text{C}$	2.480	2.500	2.508	V
Reverse Breakdown Voltage Change with Current	$400 \mu A \le I_R \le 10 mA$	(-)	2.6 3.0	10 12	mV mV
Reverse Dynamic Impedance	I _R = 1.0 mA	-	0.2 0.4	1.0 1.4	Ω Ω
Temperature Stability Avgerage Temperature Coefficient	$0^{\circ}\text{C} \le \text{T}_{\text{A}} \le 70^{\circ}\text{C}$, Note 3 $0^{\circ}\text{C} \le \text{T}_{\text{A}} \le 70^{\circ}\text{C}$, Note 3	5	- -	_ _	mV ppm/°C
Long Term Stabilty	$T_A = 25^{\circ}\text{C} \pm 0.1 \text{ C}, I_R = 1.0 \text{ mA}$	-	20	_	ppm/kHr

- † Denotes the specifications which apply over full operating temperature range.
- 3. Average temperature coefficient is defined as the total voltage change divided by the specified temperature range.

TYPICAL PERFORMANCE CHARACTERISTICS

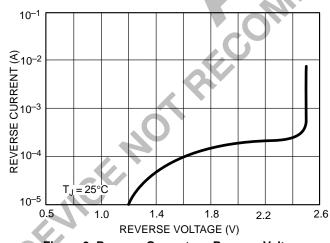


Figure 3. Reverse Current vs. Reverse Voltage

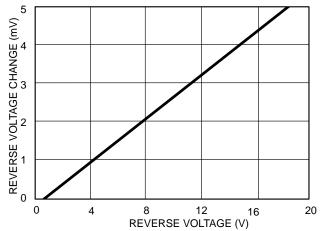
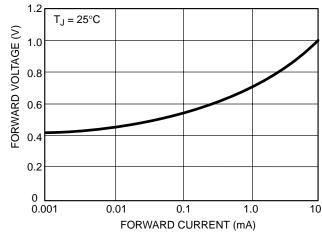


Figure 4. Change in Reverse Voltage vs.
Reverse Current

^{2. 60} second maximum above 183°C.

^{*}The maximum package power dissipation must be observed.



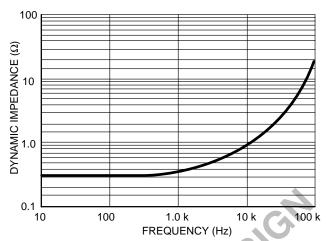
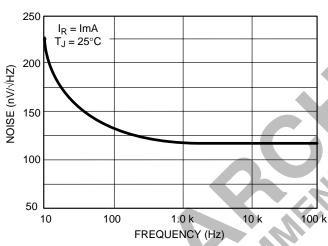


Figure 5. Forward Voltage vs. Forward Current

Figure 6. Dynamic Impedance vs. Frequency



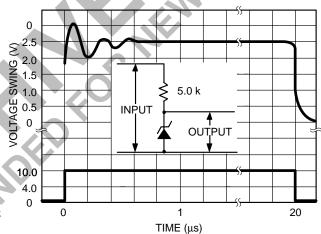


Figure 7. Zener Noise Voltage vs. Frequency

Figure 8. Response Time

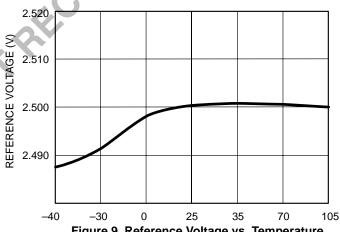
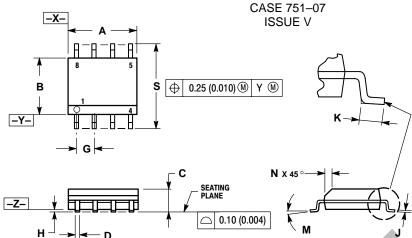


Figure 9. Reference Voltage vs. Temperature

PACKAGE DIMENSIONS

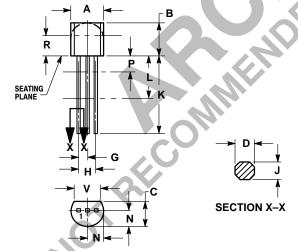
SO-8 **D SUFFIX**





	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27 BSC		0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
M	0 0	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S 4	5.80	6.20	0.228	0.244	

TO-92 Z SUFFIX CASE 29-11 ISSUE AL



⊕ 0.25 (0.010) M Z Y S X S

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

PACKAGE THERMAL DATA

Parameter		SO-8	TO-92	Unit
$R_{\Theta JC}$	Typical	45	-	°C/W
$R_{\Theta JA}$	Typical	165	170	°C/W

Notes



Notes





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